

Supporting information

Broadband Full-Stokes Polarimeter based on ReS₂ Nanobelts

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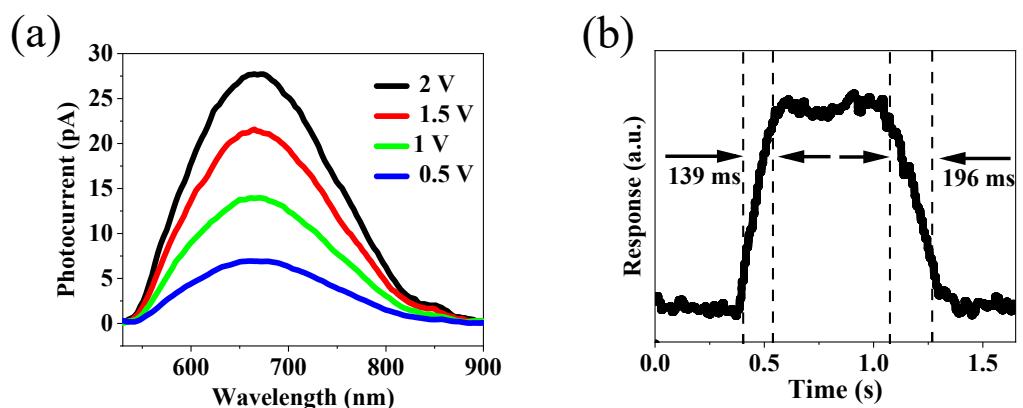


Fig. S1. (a) The spectral response of the ReS_2 device under biases of 2, 1.5, 1 and 0.5 V. (b) The response speed of the device measured by an oscilloscope under a bias voltage of 0.5 V illuminated by a 665 nm light.

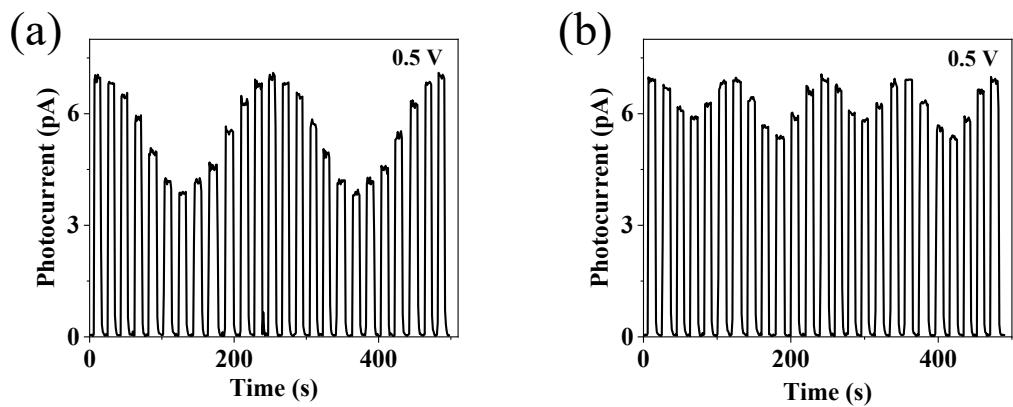


Fig. S2. (a) Time-dependent photoresponse with polarization direction of incident light from $0\text{--}360^\circ$ under a 665 nm light excitation. (b) The time-dependent photocurrent with the incident light from $0\text{--}360^\circ$ by rotating quart-wave plate under a 665 nm light illumination.

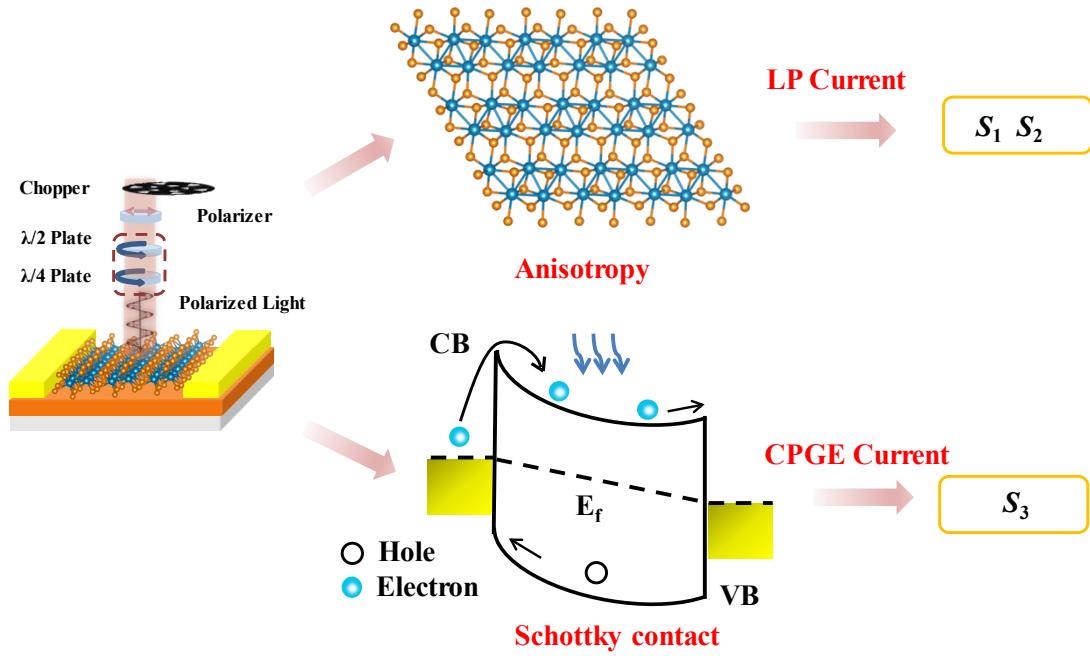


Fig. S3. The schematic illustration of the measurement mechanism for the ReS₂ nanobelt full-Stokes polarimeter^[1-3].

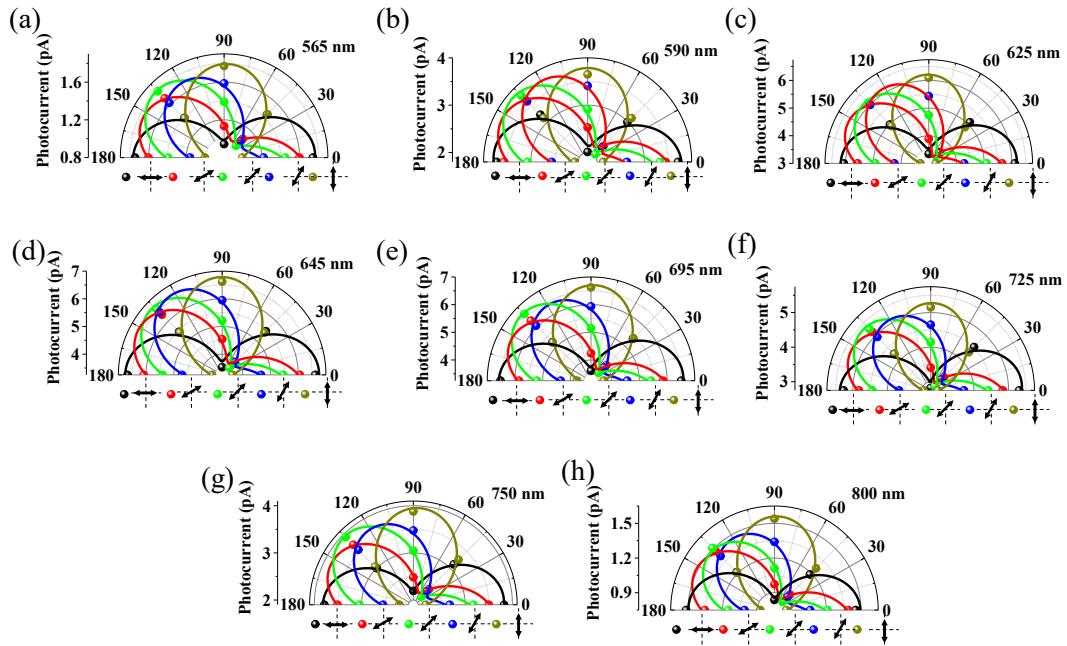


Fig. S4. Measured photocurrent of ReS_2 nanobelt device under five different linearly polarized light with different wavelength illumination when the rotation angle is set to 0° , 45° , 90° , 135° and 180° .

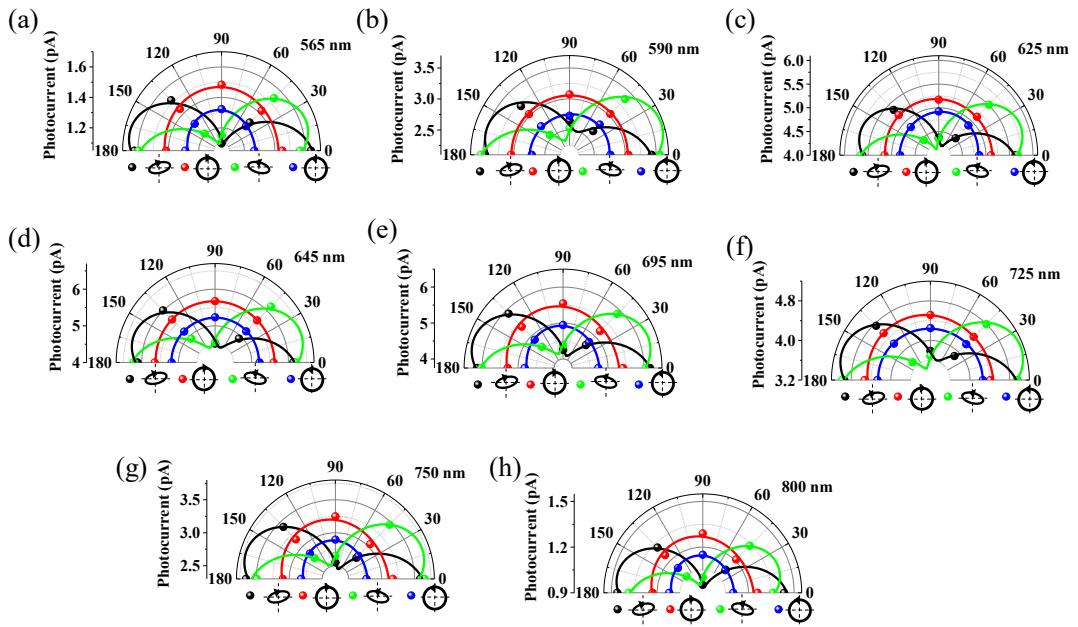


Fig. S5. Measured photocurrent of ReS_2 nanobelt device under different polarized (elliptically and circularly polarized) light with different wavelength illumination when the rotation angle is set to 0° , 45° , 90° , 135° and 180° .

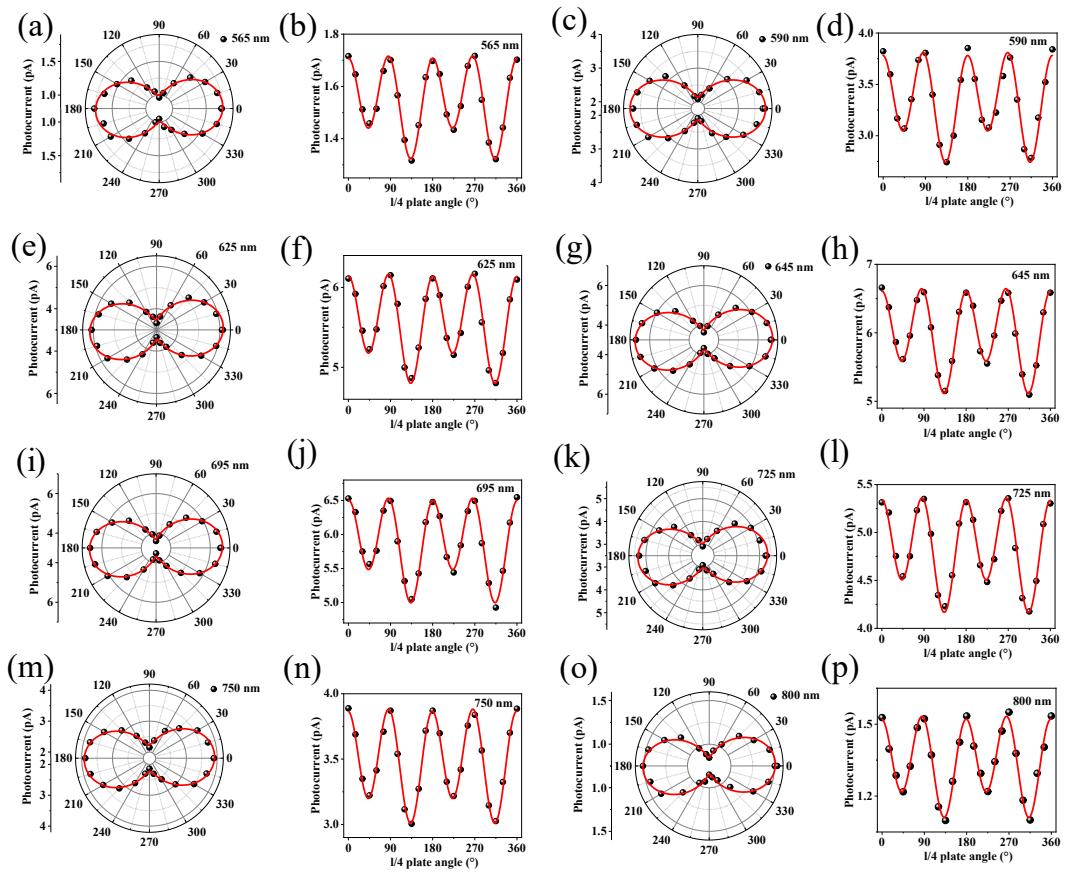


Fig. S6. The plot of the photocurrent versus the polarization angle in the polar coordinate with different wavelength illumination and the photocurrent as a function of the quarter-wave plate angle with different wavelength illumination.

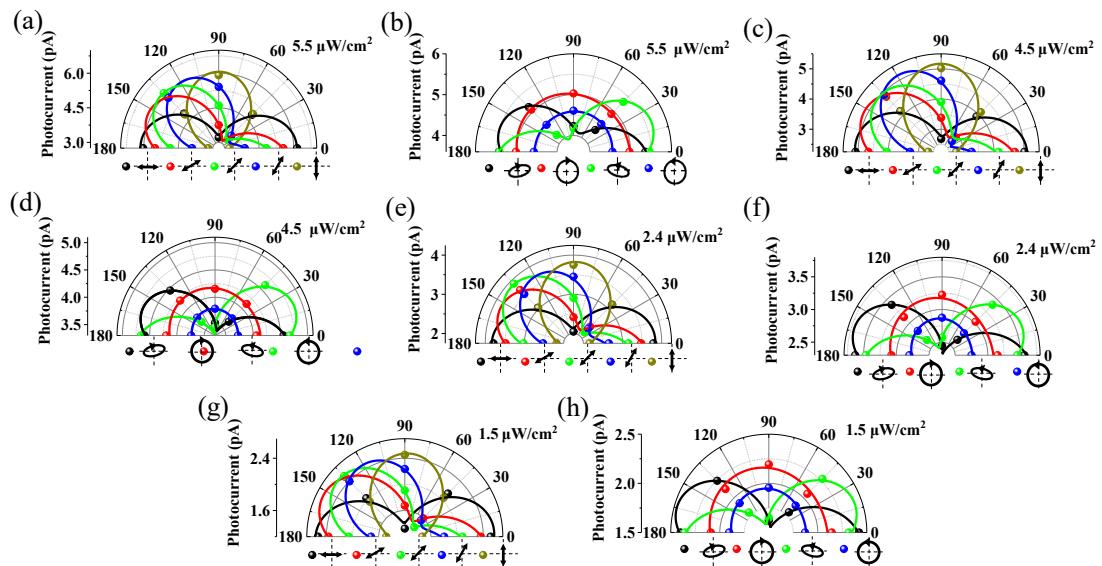


Fig. S7. Measured photocurrent of ReS₂ nanobelt device under different polarized (elliptically and circularly polarized) light with different power intensity illumination when the rotation angle is set to 0°, 45°, 90°, 135° and 180°.

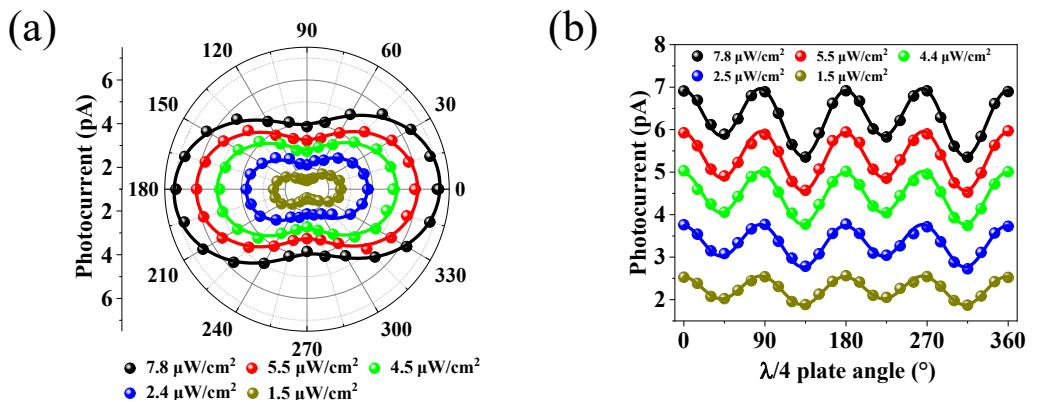


Fig. S8. The plot of the photocurrent versus the polarization angle in the polar coordinate under different power density illumination and the photocurrent as a function of the quarter-wave plate angle under different power density illumination.

Table S1. Performance of the reported on polarization-sensitive photodetectors based on two-dimensional materials

| Material | linear dichroism | Wavelength (nm) | Responsivity | Ref |
|-------------------|------------------|--------------------|-----------------------|-----|
| ReSe ₂ | 2 | 633 | 1.5 mA/W | [4] |
| GeSe | 2.2 | 808 | 1.6×10^5 A/W | [5] |
| GeS ₂ | 2.1 | 325 | - | [6] |
| GeP | 1.8 | 532 | 3.11 A/W | [7] |
| PdSe ₂ | 2.2 | 369 | 14.5 | [8] |
| NbS ₃ | 1.8 | 830 | 0.025 | [9] |
| Our work | 1.8 | 665 | 181 A/W | |

References

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